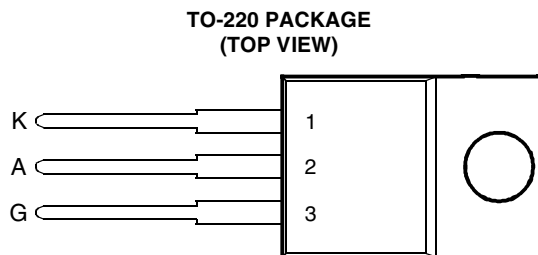


- 5 A Continuous On-State Current
- 30 A Surge-Current
- Glass Passivated Wafer
- 400 V to 800 V Off-State Voltage
- Max I_{GT} of 200 μ A



Pin 2 is in electrical contact with the mounting base.

MDC1ACA

absolute maximum ratings over operating case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Repetitive peak off-state voltage (see Note 1)	TIC106D	V_{DRM}	400	V
	TIC106M		600	
	TIC106S		700	
	TIC106N		800	
Repetitive peak reverse voltage	TIC106D	V_{RRM}	400	V
	TIC106M		600	
	TIC106S		700	
	TIC106N		800	
Continuous on-state current at (or below) 80°C case temperature (see Note 2)		$I_{T(RMS)}$	5	A
Average on-state current (180° conduction angle) at (or below) 80°C case temperature (see Note 3)		$I_{T(AV)}$	3.2	A
Surge on-state current at (or below) 25°C (see Note 4)		I_{TSM}	30	A
Peak positive gate current (pulse width $\leq 300 \mu$ s)		I_{GM}	0.2	A
Peak gate power dissipation (pulse width $\leq 300 \mu$ s)		P_{GM}	1.3	W
Average gate power dissipation (see Note 5)		$P_{G(AV)}$	0.3	W
Operating case temperature range		T_C	-40 to +110	°C
Storage temperature range		T_{stg}	-40 to +125	°C
Lead temperature 1.6 mm from case for 10 seconds		T_L	230	°C

- NOTES: 1. These values apply when the gate-cathode resistance $R_{GK} = 1 \text{ k}\Omega$.
2. These values apply for continuous dc operation with resistive load. Above 80°C derate linearly to zero at 110°C.
3. This value may be applied continuously under single phase 50 Hz half-sine-wave operation with resistive load. Above 80°C derate linearly to zero at 110°C.
4. This value applies for one 50 Hz half-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.
5. This value applies for a maximum averaging time of 20 ms.

PRODUCT INFORMATION

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
I_{DRM}	Repetitive peak off-state current	$V_D = \text{rated } V_{DRM}$	$R_{GK} = 1 \text{ k}\Omega$	$T_C = 110^\circ\text{C}$			400	μA
I_{RRM}	Repetitive peak reverse current	$V_R = \text{rated } V_{RRM}$	$I_G = 0$	$T_C = 110^\circ\text{C}$			1	mA
I_{GT}	Gate trigger current	$V_{AA} = 12 \text{ V}$	$R_L = 100 \Omega$	$t_{p(g)} \geq 20 \mu\text{s}$		5	200	μA
V_{GT}	Gate trigger voltage	$V_{AA} = 12 \text{ V}$ $t_{p(g)} \geq 20 \mu\text{s}$	$R_L = 100 \Omega$ $R_{GK} = 1 \text{ k}\Omega$	$T_C = -40^\circ\text{C}$			1.2	V
		$V_{AA} = 12 \text{ V}$ $t_{p(g)} \geq 20 \mu\text{s}$	$R_L = 100 \Omega$ $R_{GK} = 1 \text{ k}\Omega$		0.4	0.6	1	
		$V_{AA} = 12 \text{ V}$ $t_{p(g)} \geq 20 \mu\text{s}$	$R_L = 100 \Omega$ $R_{GK} = 1 \text{ k}\Omega$	$T_C = 110^\circ\text{C}$	0.2			
I_H	Holding current	$V_{AA} = 12 \text{ V}$ Initiating $I_T = 10 \text{ mA}$	$R_{GK} = 1 \text{ k}\Omega$	$T_C = -40^\circ\text{C}$			8	mA
		$V_{AA} = 12 \text{ V}$ Initiating $I_T = 10 \text{ mA}$	$R_{GK} = 1 \text{ k}\Omega$				5	
V_T	Peak on-state voltage	$I_T = 5 \text{ A}$	(See Note 6)				1.7	V
dv/dt	Critical rate of rise of off-state voltage	$V_D = \text{rated } V_D$	$R_{GK} = 1 \text{ k}\Omega$	$T_C = 110^\circ\text{C}$		10		V/ μs

NOTE 6: This parameter must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$. Voltage sensing-contacts, separate from the current carrying contacts, are located within 3.2 mm from the device body.

thermal characteristics

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			3.5	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction to free air thermal resistance			62.5	$^\circ\text{C/W}$

THERMAL INFORMATION

**AVERAGE ANODE ON-STATE CURRENT
DERATING CURVE**

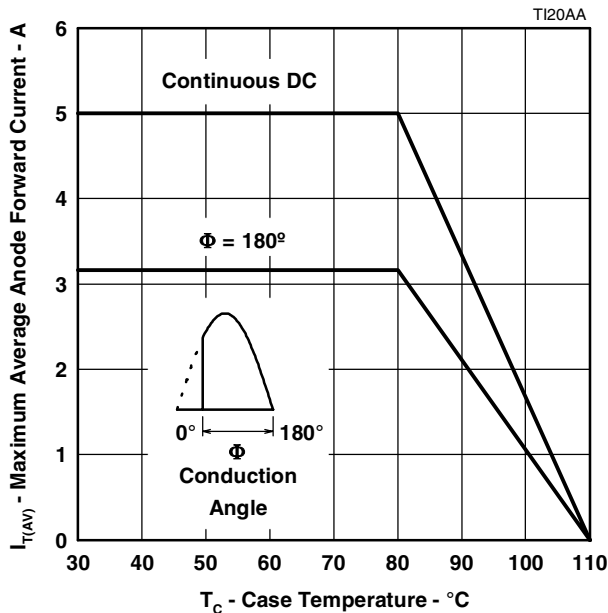


Figure 1.

**ANODE POWER DISSIPATED
vs
ON-STATE CURRENT**

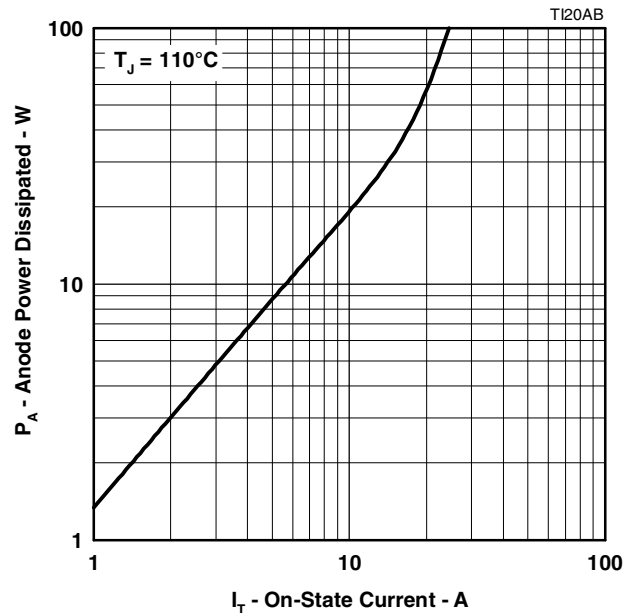


Figure 2.

**SURGE ON-STATE CURRENT
vs
CYCLES OF CURRENT DURATION**

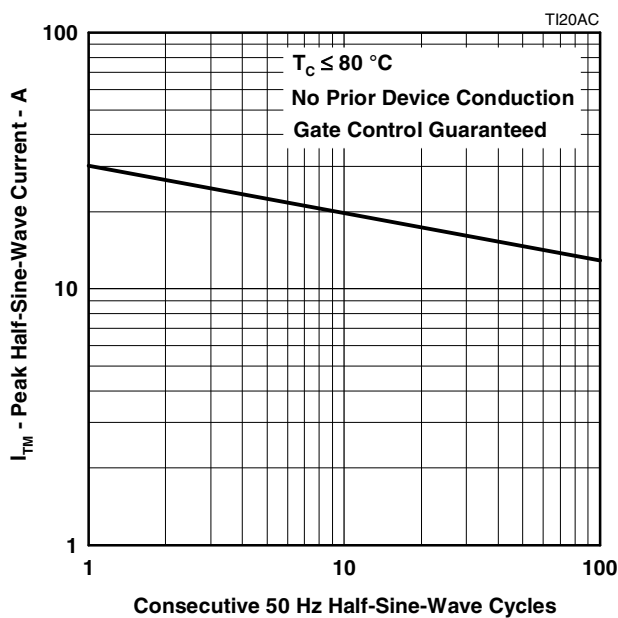


Figure 3.

**TRANSIENT THERMAL RESISTANCE
vs
CYCLES OF CURRENT DURATION**

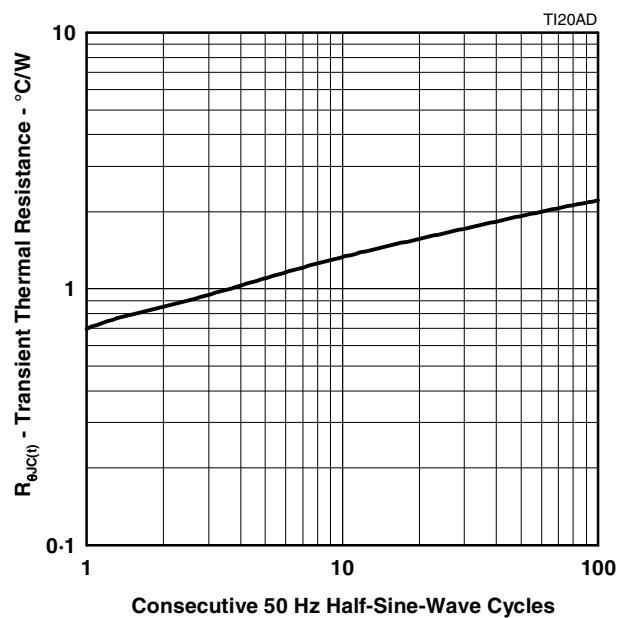


Figure 4.

PRODUCT INFORMATION

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TYPICAL CHARACTERISTICS

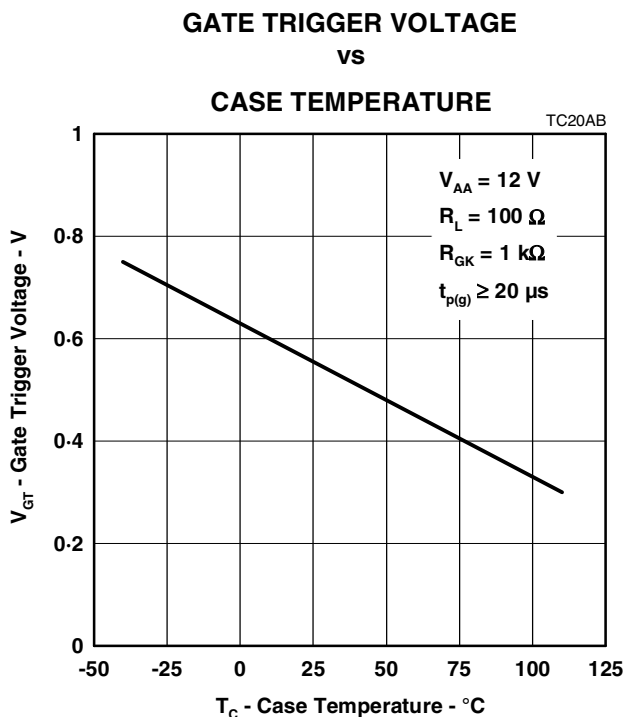


Figure 5.

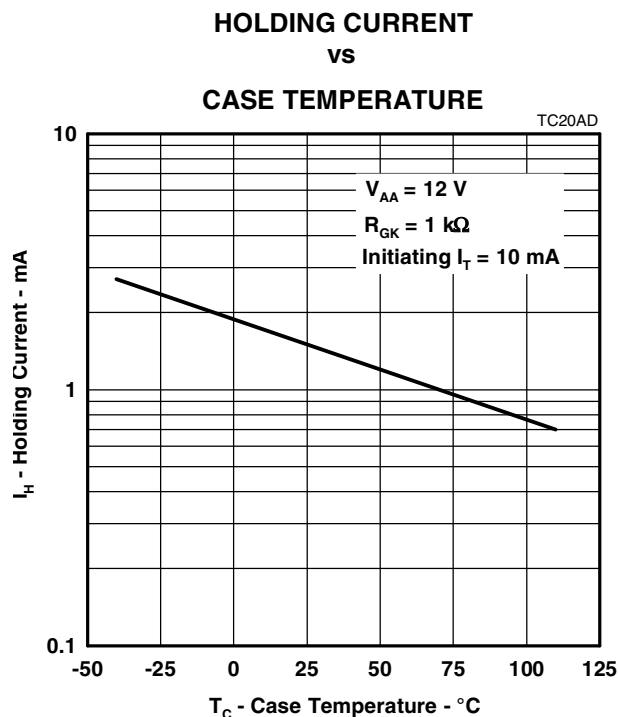


Figure 6.

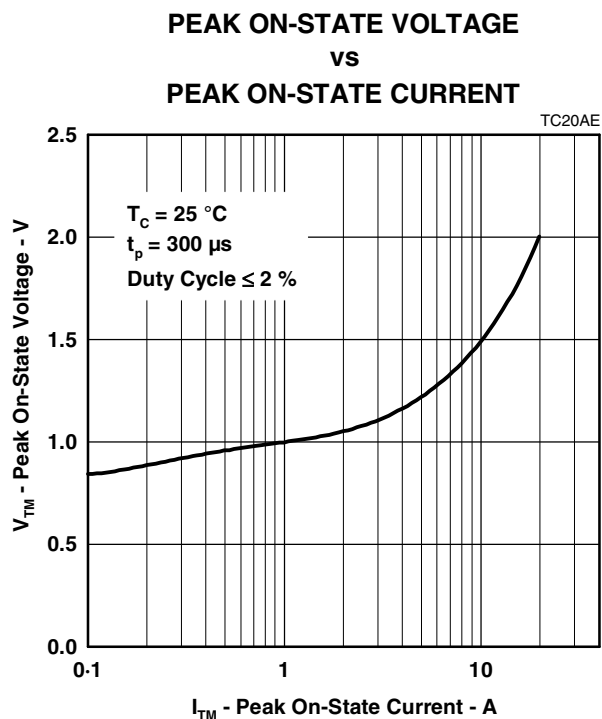


Figure 7.

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